MAX44290 Evaluation Kit

General Description

The MAX44290 evaluation kit (EV kit) provides a proven design to evaluate the MAX44290 low-offset, low-power, rail-to-rail I/O operational amplifier in 6-pin wafer-level package (WLP). The EV kit circuit is preconfigured as noninverting amplifiers, but can be adapted to other topologies by changing a few components.

The EV kit comes with a MAX44290ANT+ installed.

Features

- Accommodates Multiple Op Amp Configurations
- Component Pads Allow for Sallen-Key Filter
- Accommodates Easy-to-Use Components
- Proven PCB Layout
- Fully Assembled and Tested

Quick Start

Required Equipment

- MAX44290 EV kit
- +1.8V to +5.5V, 10mA DC power supply
- Precision voltage source
- Digital multimeter

Procedure

The EV kit is fully assembled and tested. Follow the steps below to verify board operation:

1) Verify that all jumpers (JU1–JU3) are in their default positions, as shown in Table 1.
2) Set the power supply to +5V. Connect the positive terminal of the power supply to V_{DD} and the negative terminal to GND.
3) Connect the positive terminal of the precision voltage source to INP. Connect the negative terminal of the precision voltage source to GND. INM is already connected to GND through jumper JU1.
4) Connect the DMM to monitor the voltage on OUT. With the 10kΩ feedback resistors and 1kΩ series resistors, the gain of the noninverting amplifier is +11V/V.
5) Turn on the power supply.
6) Apply 100mV from the precision voltage sources. Observe the output at OUT on the DMM that reads approximately +1.1V.

***Ordering Information* appears at end of data sheet.**

19-8086; Rev 0; 11/15

Detailed Description of Hardware

The MAX44290 EV kit provides a proven layout for the MAX44290 low-power op amp. The device is a single-supply op amp that is ideal for sensor interfaces, loop-powered systems, and various types of medical and data-acquisition instruments.

The default configuration for the device in the EV kit is in a noninverting configuration.

Op-Amp Configurations

The device is a single-supply op amp that is ideal for differential sensing, noninverting amplification, buffering, and filtering. A few common configurations are shown in the next few sections.

The following sections explain how to configure the op amp.

Noninverting Configuration

The EV kit comes preconfigured as a noninverting amplifier. The gain is set by the ratio of R5 and R1. The EV kit comes preconfigured for a gain of +11V/V. The output voltage for the noninverting configuration is given by the equation below:

$$V_{OUT} = (1+\frac{R5}{R1})[V_{INP} \pm V_{OS}]$$

Inverting Configuration

To configure the EV kit as an inverting amplifier, remove the shunt on jumper JU1 and install a shunt on jumper JU2 and feed an input signal on the INAM PCB pad.

Differential Amplifier

To configure the EV kit as a differential amplifier, replace R1–R3 and R5 with appropriate resistors. When R1 = R2 and R3 = R5, the CMRR of the differential amplifier is determined by the matching of the resistor ratios R1/R2 and R3/R5.

$$V_{OUT} = GAIN(V_{INP} - V_{INM})$$

where:

$$GAIN = \frac{R5}{R1} = \frac{R3}{R2}$$

Sallen-Key Configuration

The Sallen-Key topology is ideal for filtering sensor signals with a second-order filter and acting as a buffer. Schematic complexity is reduced by combining the filter and buffer operations. The EV kit can be configured in a Sallen-Key topology by replacing and populating a few components. The Sallen-Key topology can be configured as a unity-gain buffer by replacing R5 with a 0Ω resistor and removing resistor R1. The signal is noninverting and applied to INAP. The filter component pads are R2–R4 and R8, where some have to be populated with resistors and others with capacitors.

Lowpass Sallen-Key Filter: To configure the Sallen-Key as a lowpass filter, remove the shunt from jumper JU1, populate the R2 and R8 pads with resistors, and populate the R3 and R4 pads with capacitors. The corner frequency and Q are then given by:

$$f_C = \frac{1}{2\pi\sqrt{R_{R2}R_{R8}C_{R3}C_{R4}}}$$

$$Q = \frac{\sqrt{R_{R2}R_{R8}C_{R3}C_{R4}}}{C_{R3}(R_{R2}+R_{R8})}$$

Highpass Sallen-Key Filter: To configure the Sallen-Key as a highpass filter, remove the shunt from jumper JU1, populate the R3 and R4 pads with resistors, and populate the R2 and R8 pads with capacitors. The corner frequency and Q are then given by:

$$f_C = \frac{1}{2\pi\sqrt{R_{R3}R_{R4}C_{R2}C_{R8}}}$$

$$Q = \frac{\sqrt{R_{R3}R_{R4}C_{R2}C_{R8}}}{R_{R4}(C_{R2}+C_{R8})}$$

Bandpass Sallen-Key Filter: To configure the Sallen-Key as a bandpass filter, remove the shunt from jumper JU1, replace R8, populate the R3 and R4 pads with resistors, and populate the C8 and R2 pads with capacitors. The corner frequency and Q are then given by:

$$f_C = \frac{1}{2\pi}\sqrt{\frac{R_{R4} + R_{R8}}{C_{C8}C_{R2}R_{R8}R_{R3}R_{R4}}}$$

$$Q = \frac{\sqrt{(R_{R4} + R_{R8})C_{C8}C_{R2}R_{R8}R_{R3}R_{R4}}}{R_{R4}R_{R8}(C_{C8} + C_{R2}) + R_{R3}C_{R2}(R_{R4} - \frac{R_{R5}}{R_{R1}}R_{R8})}$$

Transimpedance Amplifier (TIA)

To configure the EV kit as a TIA, place a shunt on jumper JU2 and replace R1 with 0Ω resistors. The output voltage of the TIA is the input current multiplied by the feedback resistor:

$$V_{OUT} = -(I_{IN} + I_{BIAS}) \times R_{R5} \pm V_{OS}$$

where:

I_{IN} is the input current source applied at the INP test point

I_{BIAS} is the input bias current

V_{OS} is the input offset voltage of the op amp

Use a capacitor and 0Ω resistor at location R10 or R17 (and C8, if applicable) to stabilize the op amp by rolling off high-frequency gain due to a large cable capacitance.

Capacitive Loads

Some applications require driving large capacitive loads. The EV kit provides C8 and R6 pads for an optional capacitive-load driving circuit. C8 simulates the capacitive load while R6 acts as an isolation resistor to improve the op amp's stability at higher capacitive loads. To improve the stability of the amplifier in such cases, replace R6 with a suitable resistor value to improve amplifier phase margin

Table 1. Jumper Descriptions (JU1–JU3)

JUMPER	SHUNT POSITION	DESCRIPTION
JU1	Pin 1	Disconnects INM from GND
	1-2*	Connects IN- to GND through R1 for noninverting configuration
JU2	Pin 1*	Disconnects INAP from GND
	1-2	Connects IN+ to GND through R2
JU3	1-2*	Connects $\overline{SHDN}$ to V_{DD} to place device into normal operation
	2-3	Connects $\overline{SHDN}$ to GND to place device into shutdown operation

**Default position.*

Component List

See the links below for component information, PCB layout, and schematic.

- **MAX44290 EV BOM**
- **MAX44290 EV PCB Layout**
- **MAX44290 EV Schematic**

Ordering Information

PART	TYPE
MAX44290EVKIT#	EV Kit

#Denotes RoHS compliant.

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	11/15	Initial release	—

MAX44290 Bill of Materials (BOM) Rev 0; 11/15

ITEM	REF_DES	DNI/ DNP	QTY	MFG PART #	MANUFACTURER	VALUE	DESCRIPTION	COMMENTS
1	C1	-	1	C1608C0G1H103J; CGA3E2C0G1H103J080AD; GRM1885C1H103JA01	TDK; MURATA	0.01UF	CAPACITOR; SMT (0603); CERAMIC CHIP; 0.01UF; 50V; TOL=5%; TG=-55 DEGC to +125 DEGC; TC=C0G	
2	C2	-	1	08053C105JAT2A	AVX	1UF	CAPACITOR; SMT (0805); CERAMIC CHIP; 1UF; 25V; TOL=5%; MODEL=X7R; TG=-55 DEGC TO +85 DEGC; TC=+/-	
3	GND, TP0_GND, TP4_GND, TP6_GND	-	4	5011	?	5011	TEST POINT; PIN DIA=0.125IN; TOTAL LENGTH=0.445IN; BOARD HOLE=0.063IN; BLACK; PHOSPHOR BRONZE WIRE SILVER PLATE FINISH;	
4	JU1, JU2	-	2	PCC02SAAN	SULLINS	PCC02SAAN	CONNECTOR; MALE; THROUGH HOLE; BREAKAWAY; STRAIGHT THROUGH; 2PINS; -65 DEGC TO +125 DEGC	
5	JU3	-	1	PCC03SAAN	SULLINS	PCC03SAAN	CONNECTOR; MALE; THROUGH HOLE; BREAKAWAY; STRAIGHT THROUGH; 3PINS; -65 DEGC TO +125 DEGC	
6	R1	-	1	CRCW06031001FK; ERJ-3EKF1001V	VISHAY DALE; PANASONIC	1K	RESISTOR; 0603; 1K; 1%; 100PPM; 0.10W; THICK FILM	

7	R2, R6, R8, R12	-	4	RC1608J000CS; CR0603-J/-000ELF;RC0603JR-070RL	SAMSUNG ELECTRONICS/BOURNS/YAGEO PH	0	RESISTOR; 0603; 0 OHM; 5%; JUMPER; 0.10W; THICK FILM	
8	R5	-	1	CRCW0603 10K0FK; 9C06031A1002FK; ERJ-3EKF1002	VISHAY DALE/YAGEO PHICOMP/PANASONIC	10K	RESISTOR; 0603; 10K; 1%; 100PPM; 0.10W; THICK FILM	
9	S1-S3	-	3	STC02SYAN	SULLINS ELECTRONICS CORP.	STC02SYAN	TEST POINT; JUMPER; STR; TOTAL LENGTH=0.256IN; BLACK; INSULATION=PBT CONTACT=PHOSPHOR BRONZE; COPPER PLATED TIN OVERALL	
10	TP1	-	1	5000	KEYSTONE	N/A	TEST POINT; PIN DIA=0.1IN; TOTAL LENGTH=0.3IN; BOARD HOLE=0.04IN; RED; PHOSPHOR BRONZE WIRE SILVER PLATE FINISH;	
11	TP_INM, TP_OUT, TP_INAP	-	3	5012	?	5012	TEST POINT; PIN DIA=0.125IN; TOTAL LENGTH=0.445IN; BOARD HOLE=0.063IN; WHITE; PHOSPHOR BRONZE WIRE SILVER PLATE FINISH;	
12	U1	-	1	MAX44290AWT+	MAXIM	MAX44290AWT+	EVKIT PART - IC; MAX44290; WLP6; PKG. CODE: N60C1+1	
13	VDD	-	1	5010	KEYSTONE	N/A	TESTPOINT WITH 1.80MM HOLE DIA, RED, MULTIPURPOSE;	
14	C3, C6, C8	DNP	3	N/A	N/A	OPEN	PACKAGE OUTLINE 0603 NON-POLAR CAPACITOR	

15	C4, C5, C9	DNP	3	N/A	N/A	SHORT	PACKAGE OUTLINE 0603 NON-POLAR CAPACITOR	
16	INM, INP, OUT	DNP	3	CN-BNC-011PG	FIRST TECH ELECTRONICS, CO.	CN-BNC-011PG	CONNECTOR; FEMALE; THROUGH HOLE; BNC JACK; STRAIGHT; 5PINS	
17	R3, R4, R7, R9-R11	DNP	6	N/A	N/A	OPEN	PACKAGE OUTLINE 0603 RESISTOR	
TOTAL			39					

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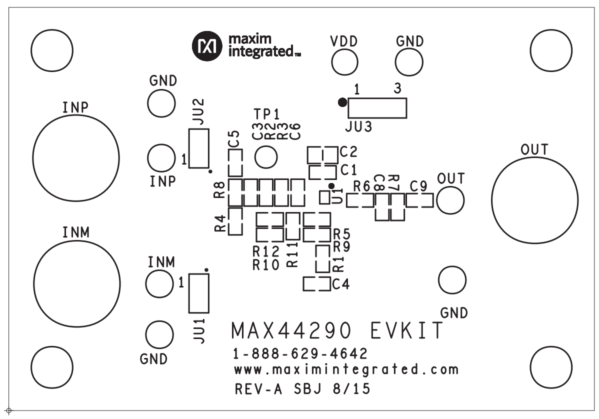
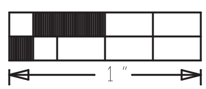
HARDWARE NAME:MAX44290_EVKIT_A

HARDWARE NUMBER:

ENGINEER: DESIGNER:

DATE: ODB++/GERBER: SILK_TOP





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HARDWARE NAME:MAX44290_EVKIT_A

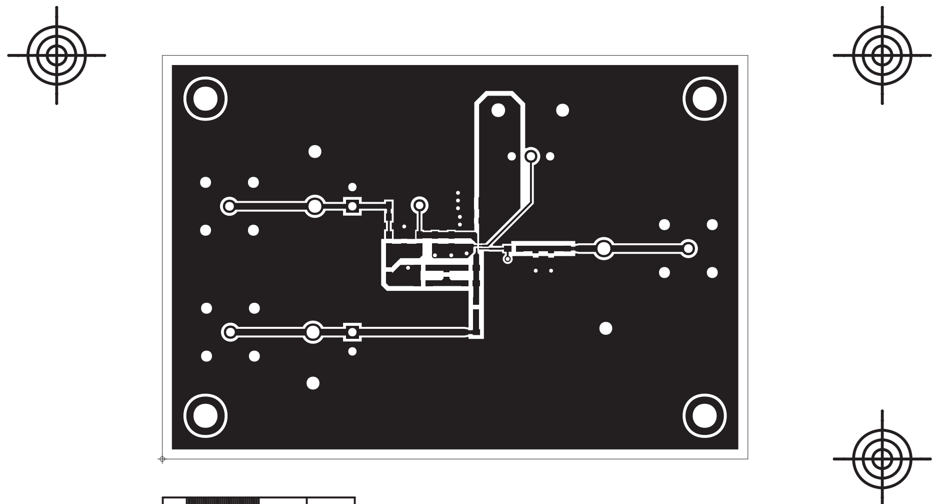
HARDWARE NUMBER:

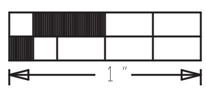
ENGINEER:I

DESIGNER:

DATE: 08/25/2015

ODB++/GERBER: TOP





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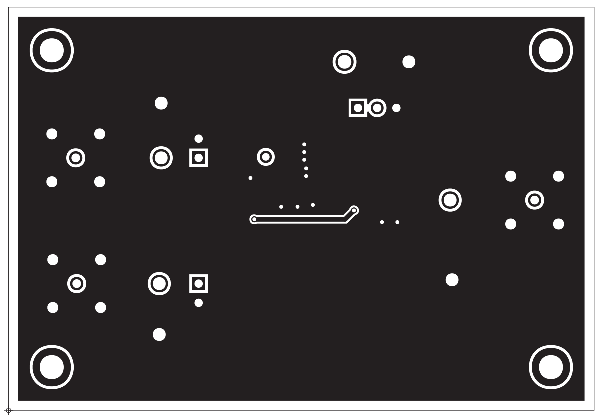
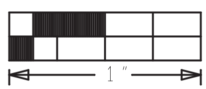
HARDWARE NAME:MAX44290_EVKIT_A

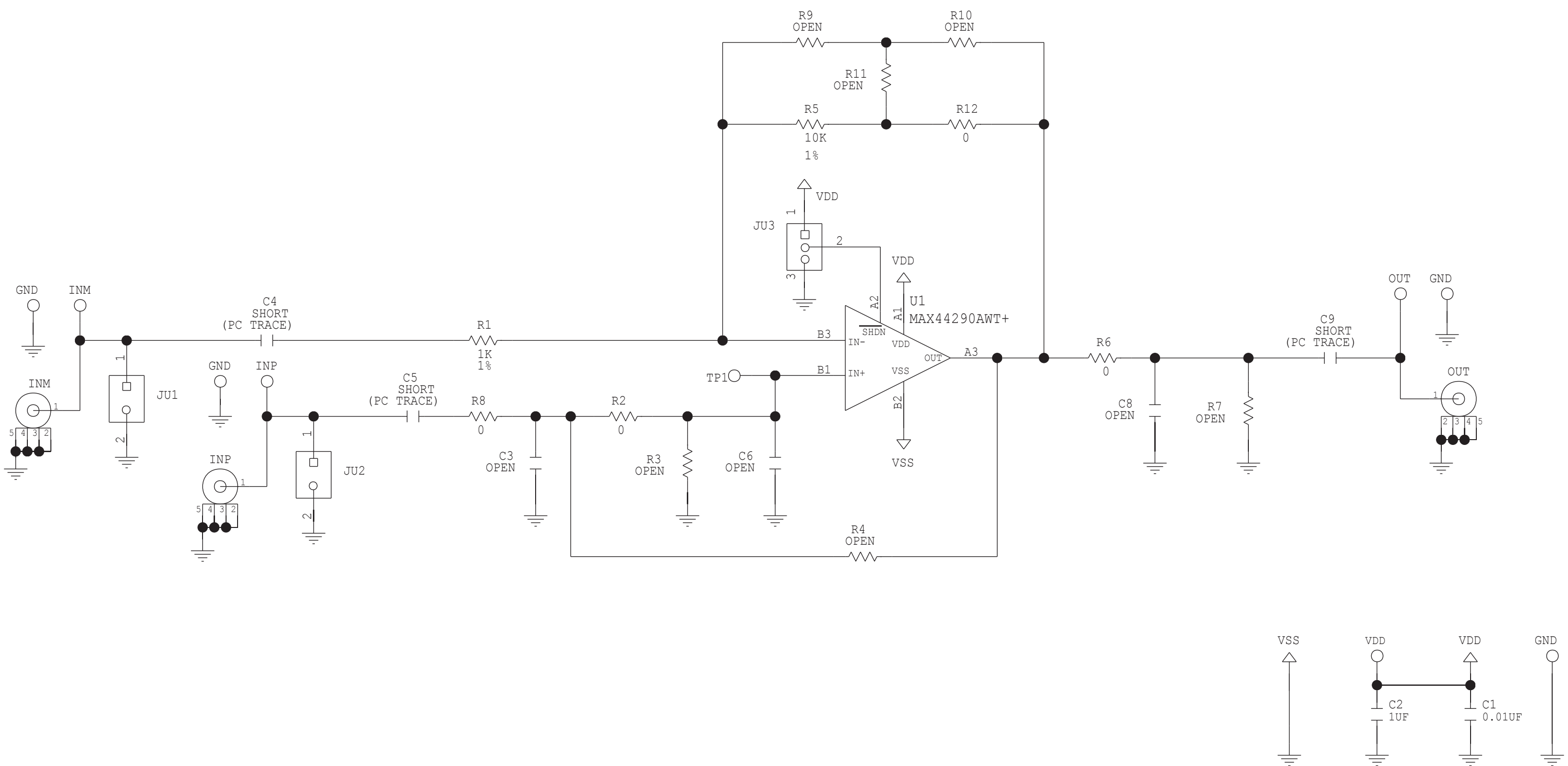
HARDWARE NUMBER:

ENGINEER: DESIGNER:

DATE: 08/25/2015 ODB++/GERBER: BOTTOM






R9
OPEN
R10
OPEN
R11
OPEN
R5
10K
1%
R12
0
VDD
JU3
U1
MAX44290AWT+
SHDN
IN-
IN+
VDD
VSS
OUT
A1
A2
A3
B1
B2
B3
GND
INM
C4
SHORT
(PC TRACE)
R1
1K
1%
JU1
INP
JU2
C5
SHORT
(PC TRACE)
R8
0
R2
0
C3
OPEN
R3
OPEN
C6
OPEN
TP1
R4
OPEN
R6
0
C8
OPEN
R7
OPEN
C9
SHORT
(PC TRACE)
OUT
VSS
C2
1UF
C1
0.01UF